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Kind regards,

Team Nexperia



BZV85 series

Voltage regulator diodes

Rev. 03 — 10 November 2009

Product data sheet

1. Product profile

1.1 General description

Medium-power voltage regulator diodes in small hermetically sealed leaded SOD66 (DO-41) glass packages.

The diodes are available in the normalized E24 approximately $\pm 5\%$ tolerance range. The series consists of 33 types with nominal working voltages from 3.6 V to 75 V.

1.2 Features

- Total power dissipation: max. 1.3 W
- Working voltage range: nominal 3.3 V to 75 V (E24 range)
- Small hermetically sealed glass package
- Tolerance series: approximately $\pm 5\%$
- Non-repetitive peak reverse power dissipation: max. 60 W

1.3 Applications

- Stabilization purposes

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	$I_F = 50\text{ mA}$	-	-	1	V
P_{tot}	total power dissipation	$T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$; lead length 10 mm	[1]	-	1	W
			[2]	-	1.3	W
			[3]	-	60	W
P_{ZSM}	non-repetitive peak reverse power dissipation	square wave; $t_p = 100\text{ }\mu\text{s}$				

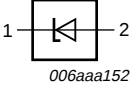
[1] Device mounted on a Printed-Circuit Board (PCB) with 1 cm² copper area per lead.

[2] If the leads are kept at $T_{\text{tp}} = 55\text{ }^{\circ}\text{C}$ at 4 mm from body.

[3] $T_j = 25\text{ }^{\circ}\text{C}$ prior to surge

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode		
2	anode		

[1] The marking band indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BZV85 series	-	hermetically sealed glass package; axial leaded; 2 leads	SOD66

[1] The series consists of 33 types with nominal working voltages from 3.3 V to 75 V.

4. Marking

Table 4. Marking codes

Type number	Marking code
BZV85 series	The diodes are type branded.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I_F	forward current		-	500	mA
I_{ZSM}	non-repetitive peak reverse current	square wave; $t_p = 100 \mu s$	[1] -	see Table 8	
		half sine wave; $t_p = 10 ms$	[1] -	see Table 8	
P_{tot}	total power dissipation	$T_{amb} = 25 \text{ }^\circ\text{C}$; lead length 10 mm	[2] -	1	W
			[3] -	1.3	W
P_{ZSM}	non-repetitive peak reverse power dissipation	square wave; $t_p = 100 \mu s$	[1] -	60	W
T_j	junction temperature		-	200	$^\circ\text{C}$
T_{stg}	storage temperature		-65	+200	$^\circ\text{C}$

[1] $T_j = 25 \text{ }^\circ\text{C}$ prior to surge

[2] Device mounted on a PCB with 1 cm² copper area per lead.

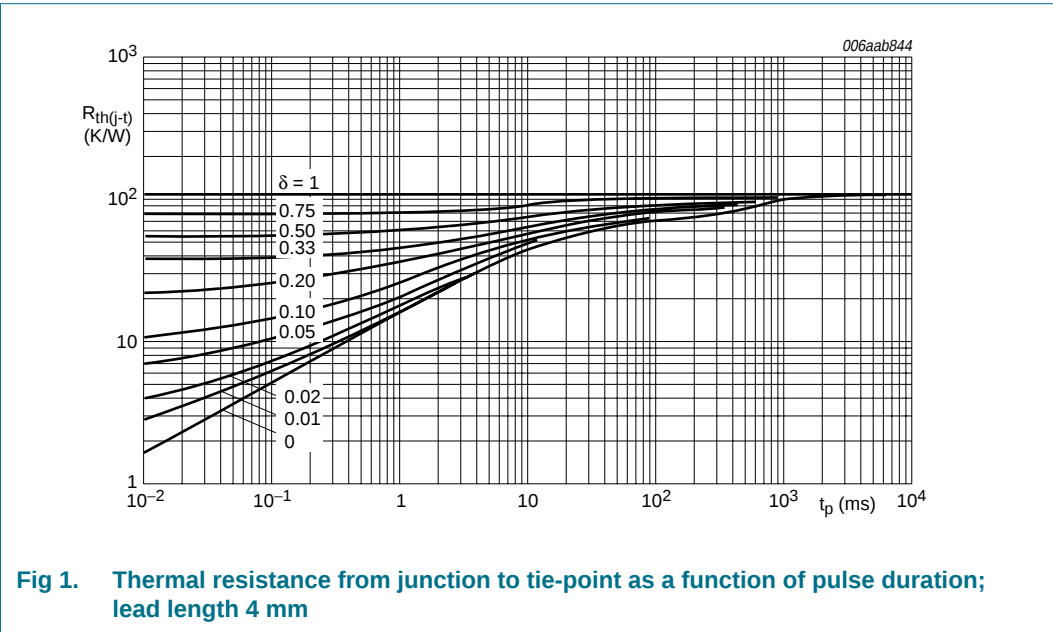
[3] If the leads are kept at $T_{ip} = 55 \text{ }^\circ\text{C}$ at 4 mm from body.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-t)}$	thermal resistance from junction to tie-point	lead length 4 mm	-	-	110	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	lead length 10 mm [1]	-	-	175	K/W

[1] Device mounted on a PCB with 1 cm² copper area per lead.



7. Characteristics

Table 7. Characteristics

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	$I_F = 50\text{ mA}$	-	-	1	V

Table 8. Characteristics per type*T_J = 25 °C unless otherwise specified.*

BZV85-Cxxx	Working voltage V _Z (V) at I _{test}		Differential resistance r _{dif} (Ω) at I _{test}	Temperature coefficient S _Z (mV/K) at I _{test}		Test current I _{test} (mA)	Diode capacitance C _d (pF) at f = 1 MHz; V _R = 0 V	Reverse current I _R (μA)		Non-repetitive peak reverse current I _{ZSM} at t _p = 100 μs; T _{amb} = 25 °C	
	Min	Max	Max	Min	Max		Max	Max	V _R (V)	Max (A)	Max (mA)
3V6	3.4	3.8	15	-3.5	-1.0	60	450	50	1.0	8.0	2000
3V9	3.7	4.1	15	-3.5	-1.0	60	450	10	1.0	8.0	1950
4V3	4.0	4.6	13	-2.7	0	50	450	5	1.0	8.0	1850
4V7	4.4	5.0	13	-2.0	0.7	45	300	3	1.0	8.0	1800
5V1	4.8	5.4	10	-0.5	2.2	45	300	3	2.0	8.0	1750
5V6	5.2	6.0	7	0	2.7	45	300	2	2.0	8.0	1700
6V2	5.8	6.6	4	0.6	3.6	35	200	2	3.0	7.0	1620
6V8	6.4	7.2	3.5	1.3	4.3	35	200	2	4.0	7.0	1550
7V5	7.0	7.9	3	2.5	5.5	35	150	1	4.5	5.0	1500
8V2	7.7	8.7	5	3.1	6.1	25	150	0.7	5.0	5.0	1400
9V1	8.5	9.6	5	3.8	7.2	25	150	0.7	6.5	4.0	1340
10	9.4	10.6	8	4.7	8.5	25	90	0.2	7.0	4.0	1200
11	10.4	11.6	10	5.3	9.3	20	85	0.2	7.7	3.0	1100
12	11.4	12.7	10	6.3	10.8	20	85	0.2	8.4	3.0	1000
13	12.4	14.1	10	7.4	12.0	20	80	0.2	9.1	3.0	900
15	13.8	15.6	15	8.9	13.6	15	75	0.05	10.5	2.5	760
16	15.3	17.1	15	10.7	15.4	15	75	0.05	11.0	1.75	700
18	16.8	19.1	20	11.8	17.1	15	70	0.05	12.5	1.75	600
20	18.8	21.2	24	13.6	19.1	10	60	0.05	14.0	1.75	540
22	20.8	23.3	25	16.6	22.1	10	60	0.05	15.5	1.5	500
24	22.8	25.6	30	18.3	24.3	10	55	0.05	17	1.5	450
27	25.1	28.9	40	20.1	27.5	8	50	0.05	19	1.2	400
30	28.0	32.0	45	22.4	32.0	8	50	0.05	21	1.2	380
33	31.0	35.0	45	24.8	35.0	8	45	0.05	23	1.0	350
36	34.0	38.0	50	27.2	39.9	8	45	0.05	25	0.9	320
39	37.0	41.0	60	29.6	43.0	6	45	0.05	27	0.8	296
43	40.0	46.0	75	34.0	48.3	6	40	0.05	30	0.7	270
47	44.0	50.0	100	37.4	52.5	4	40	0.05	33	0.6	246
51	48.0	54.0	125	40.8	56.5	4	40	0.05	36	0.5	226
56	52.0	60.0	150	46.8	63.0	4	40	0.05	39	0.4	208
62	58.0	66.0	175	52.2	72.5	4	35	0.05	43	0.4	186
68	64.0	72.0	200	60.5	81.0	4	35	0.05	48	0.35	171
75	70.0	80.0	225	66.5	88.0	4	35	0.05	53	0.3	161

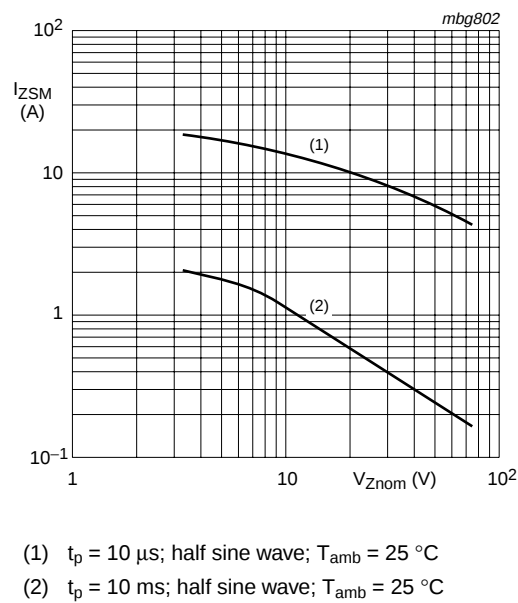


Fig 2. Non-repetitive peak reverse current as a function of the nominal working voltage

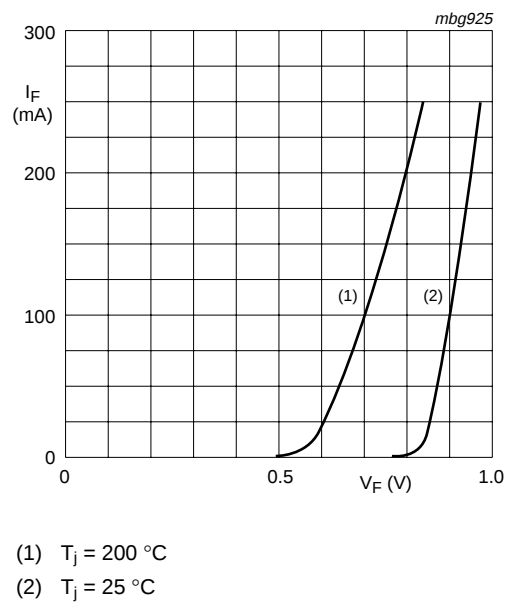


Fig 3. Forward current as a function of forward voltage; typical values

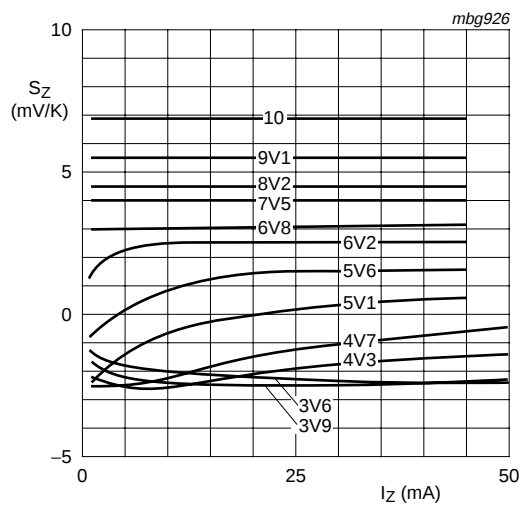


Fig 4. Temperature coefficient as a function of working current; typical values

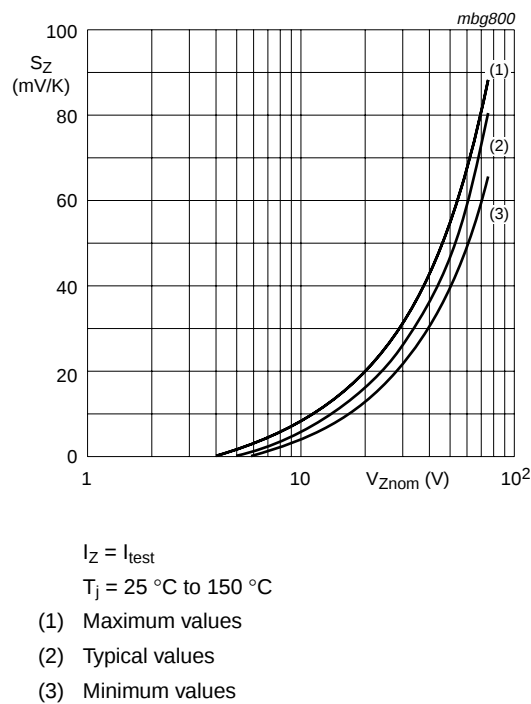


Fig 5. Temperature coefficient as a function of working current; typical values

8. Package outline

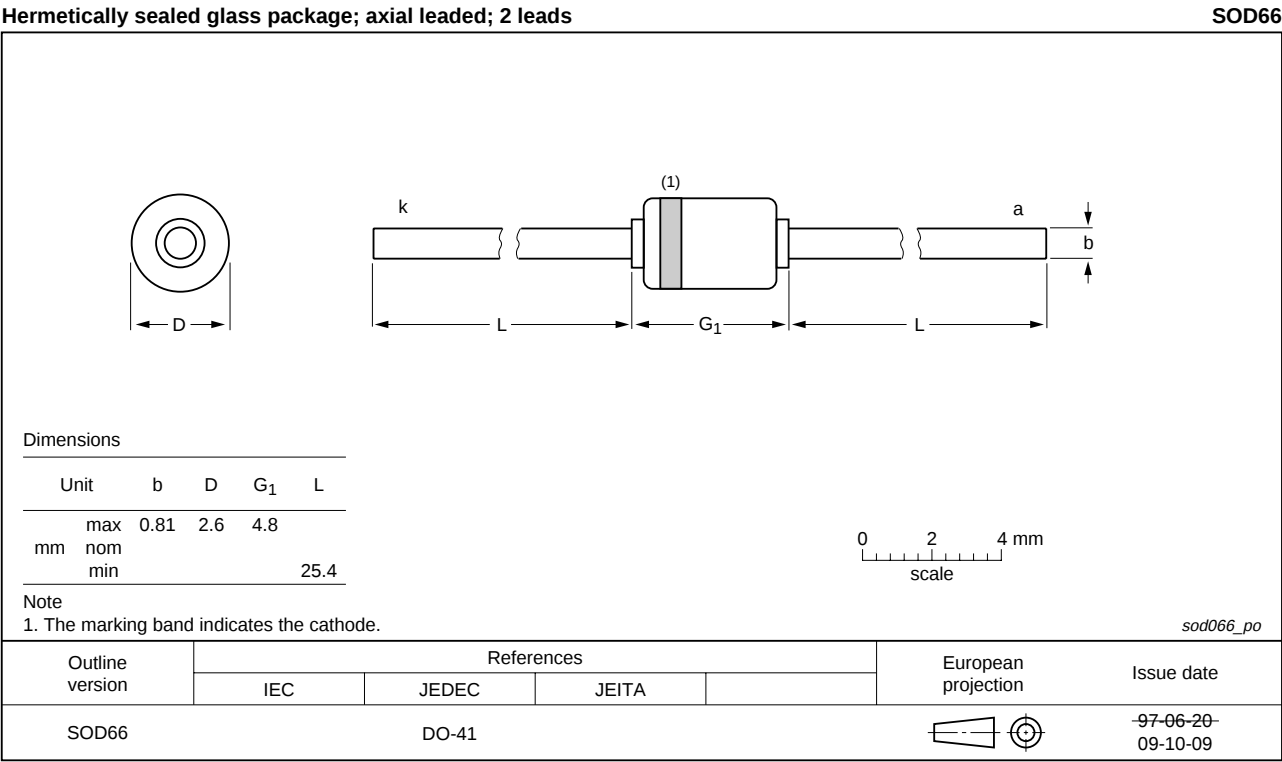


Fig 6. Package outline SOD66 (DO-41)

9. Packing information

Table 9. Packing methods
The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity
			10000
BZV85 series ^[2]	SOD66	52 mm tape ammopack, axial	-133
		52 mm reel pack, axial	-113

[1] For further information and the availability of packing methods, see [Section 11](#).
[2] The series consists of 33 types with nominal working voltages from 3.3 V to 75 V.

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BZV85_SER_3	20091110	Product data sheet	-	BZV85_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 6: $R_{th(j-tp)}$ redefined to $R_{th(j-t)}$ thermal resistance from junction to tie-point • Figure 1: $R_{th(j-tp)}$ redefined to $R_{th(j-t)}$ thermal resistance from junction to tie-point • Table 8 "Characteristics per type": I_{Ztest} redefined to I_{test} test current • Figure 6 "Package outline SOD66 (DO-41)": updated			
BZV85_2	19990511	Product specification	-	BZV85_1
BZV85_1	19960426	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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